

ATTORNEY DOCKET NO. 92-C-074D3 (STMI01-00024)
U.S. SERIAL NO. 09/858,397
PATENT

REMARKS

Claims 17-23, 25 and 46-59 are pending in the present application.

Claim 17 was amended.

Examination of the application on the merits is respectfully requested.

AMENDMENTS WITH MARKINGS TO SHOW CHANGES MADE

Claim 17 was amended herein as follows:

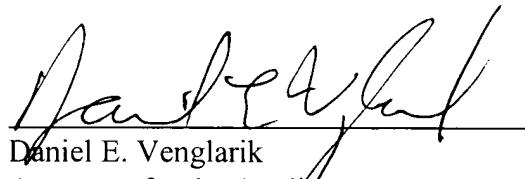
- 1 17. (twice amended) A method of fabricating a portion of a semiconductor device comprising:
- 2 forming a gate structure on a substrate by:
- 3 [depositing]forming an insulating oxide layer on the substrate;
- 4 depositing a nitride layer on the oxide layer; and
- 5 depositing a polysilicon layer on the nitride layer; and
- 6 reoxidizing the gate structure to form a layer of oxide over the gate structure.

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If any outstanding issues remain, or if the Examiner has any further suggestions for expediting prosecution of this Application, the Applicant respectfully invites the Examiner to contact the undersigned at the telephone number indicated below or at *dvenglarik@novakov.com*.

Respectfully submitted,

NOVAKOV DAVIS & MUNCK, P.C.



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